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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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ATTY. DOCKET NO.	SERIAL NO.
501.22642CC9	
APPLICANT **FUJISAKI et al**	
FILING DATE **July 23, 2003**	GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		4 5 4 4 4 1 7	10/85	Clarke			
		4 6 1 8 3 9 6	10/86	Shimoda			
		3 8 3 3 3 4 2	9/74	Holliday			
		3 4 4 6 6 0 3	5/69	Loiacono			
		3 0 3 3 6 6 0	5/62	Okkerse			
		4 2 9 9 6 5 0	11/81	Bonner			
		2 9 0 8 0 0 4	10/59	Levinson			
		4 5 3 9 0 6 7	9/85	Washizuka			
		4 5 8 6 9 7 9	5/86	Katsumata			
		4 6 3 7 8 5 4	1/87	Fukuda			
		4 6 4 5 5 6 0	2/87	Matsumoto			

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
		55 1 1 3 6 9 9	9/80	Japan			X	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		Ghandhi, S. VLSI Fabrication Principles, John Wiley, 1983 pp 86-90, 98-100
		Sze, S., Physics of Semiconductor Devices, John Wiley, 1981, p 33
		IEEE Transactions on Electron Devices, vo. ED-31, No. 8, Aug. 1984, pp 1057, para 4 5; New York, US; S. Miyazawa

EXAMINER	DATE CONSIDERED

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		4 8 6 3 5 5 4	9/89	Kawasaki			
		5 7 7 0 8 7 3	6/98	Fujisaki et al			
		6 2 9 4 8 0 4	9/01	Fujisaki et al			

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		YES	NO
	Journal of Crystal Growth, Vol. 63 no. 2, Oct. 1983 pp 415-418, Amsterdam NL; Fornari "Dislocation-free silicon-doped gallium arsenide grown by LEC Procedure		
	Terashima "Control of Growth Parameters for Obtaining Highly Uniform Large Diameter LEC GaAs" 5th Conf. On Semi-insulating III-V Materials, 1988 pp 413-422		
	Matsuoko et al "uniformity Evaluation of MESFETs for FGaAs LSI Fabrication" IEEE Trans. On Elec. Dev. Vol ED31, no. 8 Aug. 1984 pp 1062		
	Applied Physics Letters, vol 44, no. 1, Jan. 1984 pp 74-76 New York, US; Hunter "Carbon in Semi-Insulating, liquid Encapsulated Czochralski GaAs"		
	Patent Abstracts of Japan, vol. 4,no. 173 (C-32) [655], 29 Nov. 1980; JP A-55-113-669 Sumitomo 2-09-1980		

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